



Date : 1/1/2020
 Doc. No.: 2219009
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 Power Device Quality Control Dept.
 ROHM Co., Ltd.

Product/Process Change Notification

Dear Customer,
 This is an announcement of change(s) to the process being used for the products currently supplied.
 We request your acknowledgement to receive this notification within the given period.

Please reply by: 31-Mar-20

Title of change	Add 8inch wafer factory with change of the backside material to FRD chip in IGBT device.		
Affected product(s)	Product name		Customer part number
	RGT16NS65DGTL RGT30NS65DGTL RGT40NS65DGTL RGT8NS65DGTL		-
Detailed description of change	Now		After
	IGBT wafer : 6 inch factory (LAPIS semiconductor Miyazaki Co.,Ltd.) FRD chip backside material: Ti/Ni/Ag		IGBT wafer: 6 inch factory (LAPIS semiconductor Miyazaki Co.,Ltd.) Add 8 inch factory (ROHM Shiga Co.,Ltd.) FRD chip backside material: Ti/Ni/Au
Reason for change	Improve productivity and production capacity for increase production.		
Anticipated impact on quality	(form, fit, function, reliability) Electrical characteristic and reliability: No change. See attachment for detail.		
Identification of change	There is not the change of the device name, but we can traceability it by lol number code.		
Planned date of change	2020/4/1	Sample availale schedule	Please contact sales
Attachements (data, report)	Yes <input checked="" type="radio"/> No <input type="radio"/>	8 inch wafer factory addition, for listed IGBT devices	
Comments	If no reply is received before the requested date of reply, we will consider this PCN accepted by the customer.		

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